

DPAD/SSTDPAD Series

Dual Low-Leakage Pico-Amp Diodes

DPAD1 SSTDPAD5
DPAD5 SSTDPAD100
DPAD50

Product Summary

Part Number	I _R Max (pA)
DPAD1	-1
DPAD5/SSTDPAD5	-5
DPAD50	-50
SSTDPAD100	-100

Features

- Ultralow Leakage: DPAD1 < 1 pA
- Ultralow Capacitance: DPAD1 < 0.8 pF

Benefits

- Negligible Circuit Leakage Contribution
- Circuit "Transparent" Except to Shunt High-Frequency Spikes

Applications

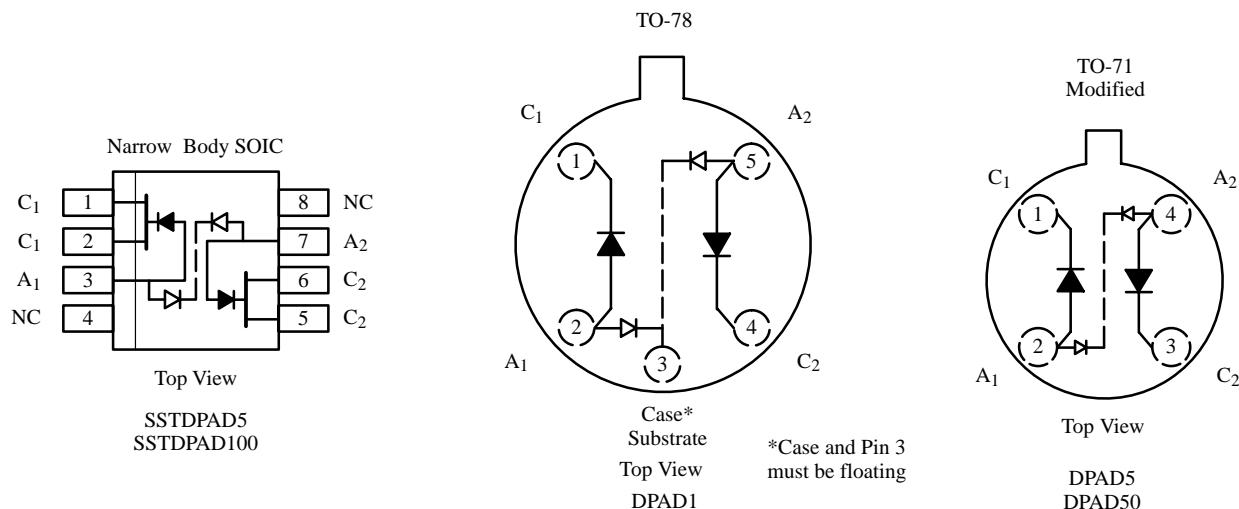
- Op Amp Input Protection
- Multiplexer Overvoltage Protection

Description

The DPAD/SSTDPAD series of extremely low-leakage diodes provides a superior alternative to conventional diode technology when reverse current (leakage) must be minimized. These devices feature leakage currents ranging from -1 pA (DPAD1) to -100 pA (SSTDPAD100) to support a wide range of applications.

The low-cost, compact, narrow-body SO-8 (SSTDPAD) package allows maximum circuit performance. Tape-and-reel options are available for automated assembly (see Packaging Information).

The TO-78 and TO-71 (DPAD) hermetically sealed metal cans are available with full military processing per MIL-S-19500 (see Military Information).



Updates to this data sheet may be obtained via facsimile by calling Siliconix FaxBack, 1-408-970-5600. Please request FaxBack document #70340.

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Absolute Maximum Ratings^a

Forward Current	50 mA	Total Device Dissipation ^b	500 mW
Storage Temperature	-55 to 150°C		
Operating Junction Temperature	-55 to 150°C		
Lead Temperature (1/16" from case for 10 sec.)	300°C		

Notes:

- a. $T_A = 25^\circ\text{C}$ unless otherwise noted.
- b. Derate 4 mW/ $^\circ\text{C}$ at 25°C .

Specifications^a

Parameter	Symbol	Test Conditions	Limits			Unit
			Min	Typ ^b	Max	
Static						
Reverse Current	I _R	V _R = -20 V	DPAD1	-0.2	-1	pA
			DPAD5/SSTDPAD5	-2	-5	
			DPAD50	-5	-50	
			SSTDPAD100	-10	-100	
Reverse Breakdown Voltage	BV _R	I _R = -1 μA	DPAD1	-45	-60	V
			DPAD5/DPAD50	-45	-55	
			SSTDPAD5/SSTDPAD100	-30	-50	
Forward Voltage Drop	V _F	I _F = 1 mA		0.8	1.5	
Dynamic						
Reverse Capacitance	C _R	V _R = -5 V, f = 1 MHz	DPAD1	0.6	0.8	pF
			DPAD5/DPAD50	1.0	2.0	
			SSTDPAD5/SSTDPAD100	2.0	4.0	
Differential Capacitance	C _{R1} - C _{R2}	V _{R1} = V _{R2} = -5 V f = 1 MHz	DPAD1	0.07	0.2	
			All Others	0.1	0.5	

Notes:

- a. $T_A = 25^\circ\text{C}$ unless otherwise noted.
- b. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

Typical Characteristics

